Unitized Semiconductor Devices - Page 1 of 2



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nclosure Material:	
letal	
verall Length:	
.250 inches	
erminal Length:	
.500 inches	
verall Diameter:	
.352 inches	
oint Electronic Device Engineering Council/jedec/case Outline Designation:	
0-5	
omponent Name And Quantity:	
transistor	
lounting Method:	
erminal	
erminal Circle Diameter:	
200 inches	
eatures Provided:	
ermetically sealed case	
emiconductor Material:	
ilicon all transistor	
oltage Rating In Volts Per Characteristic:	
.0 emitter to base voltage, static, collector open all transistor and 45.0 collector to base voltage/static/emitter open all transistor	and 45.0
ollector to emitter voltage/static/base open all transistor	
urrent Rating Per Characteristic:	
00.00 milliamperes source cutoff current all transistor	
ower Rating Per Characteristic:	
4 watts small-signal input power, common-collector preset all transistor	
laximum Operating Tempurature Per Measurement Point:	
00.0 degrees celsius junction	
pecial Features:	
Il transistor junction pattern arrangement: pnp	
recious Material And Location:	
ead surfaces gold	
recious Material:	
old	
erminal Type And Quantity:	
uninsulated wire lead	
helf Life:	
/a	
nit Of Measure:	
emilitarization:	
0	

NSN 5961-01-179-4844

Unitized Semiconductor Devices - Page 2 of 2

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